L Number	Hits	Search Text	DB	Time stamp
17	473	(polysilicon with (doped) with (undoped))	USPAT;	2002/11/03 16:5
		SAME gate	'US-PGPUB	2002/11/03 16:5
22	417	((polysilicon with (doped) with (undoped))	USPAT; US-PGPUB	2002/11/03 16:3
	200	SAME gate) and transistor	USPAT;	2002/11/03 17:0
23	302	(((polysilicon with (doped) with (undoped)) SAME gate) and transistor) and	US-PGPUB	2002/11/03 17.0
,		438/\$.ccls.	100 10100	i .
24		20010026962.URPN.	USPAT	2002/11/03 16:5
25		(gate WITH stack) with (doped) with	USPAT;	2002/11/03 17:0
		undoped	US-PGPUB	
_	125		USPAT;	2002/10/23 15:5
		"oxide/nitride/oxide") same (nitridation	US-PGPUB	
		or nitridating or nitriding or nitrided or	1	
1		nitrification or nitricate or nitridate)		2002/10/23 11:1
	68		USPAT; US-PGPUB	2002/10/23 11:1
		"oxide/nitride/oxide") same (nitridation or nitridating or nitriding or nitrided or	US-PGPUB	
:		nitrification or nitricate or nitridate)		
1) and (oxidizes or oxidize or oxidizing or		
		oxidized)		
- i	68	((("oxide nitride oxide" or ono or	USPAT;	2002/10/23 11:1
		"oxide/nitride/oxide") same (nitridation	US-PGPUB	i
		or nitridating or nitriding or nitrided or		!
ı		nitrification or nitricate or nitridate)	!	1
i) and (oxidizes or oxidize or oxidizing or		i .
1		oxidized)) and ("N.sub.20" or "N.sub.2 0"	i	
1		or "N20" or "NO")		
- }	1	("6,246,076").PN.	USPAT; US-PGPUB	2002/10/23 11:4
i		(#25C0010# #4002021# #4621277#	USPAT	2002/10/23 12:4
- i	15	("3560810" "4003071" "4621277" "4748131" "4851370" "5034798"	USFAI	2002/10/23 12.4
		"5061647" "5258333" "5286994"		İ
1		"5294820" "5364803" "5382533"	ì	İ
		"5429995" "5462812" "5552332").PN.	į	i
- 1	27	5552332.URPN.	USPAT	: 2002/10/23 12:4
- 1	9	("5296411" "5403786" "5464792"	USPAT	2002/10/23 13:2
1		"5605848" "5650344" "5661072"		
- 1		"5672521" "5851892" "6001694").PN.		
-	41	(nitrogen) WITH (diffuse or diffusing or	USPAT;	2002/10/23 13:5
[diffused) WITH oxide WITH (anneal or	US-PGPUB	
	107	annealing or heating)	USPAT;	2002/10/23 14:0
- i	107	(oxynitride or "oxy nitride" or SiON) SAME	US-PGPUB	2002/10/23 14.0
1		(nitridating or "N.sub.20" or "N.sub.2 0" or N2O or "nitrous oxide") SAME (oxidizing	03-10108	\$0.
ı		or oxidizes or oxidized or oxidating)	1	
_ 1	235	(oxynitride or "oxy nitride" or SiON) and	USPAT;	2002/10/23 14:0
i	233	((oxide or dioxide) SAME(nitridating or	US-PGPUB	
1		"N.sub.20" or "N.sub.2 0" or N20 or		
1		"nitrous oxide") SAME (oxidizing or	1	
- 1		oxidizes or oxidized or oxidating))		
- 1	99	(oxynitride or "oxy nitride" or SiON) SAME	USPAT;	2002/10/23 14:2
- 1		(nitridating or nitridation or nitriding	US-PGPUB	
		or nitrided or nitrification or nitricate	1	
		or nitridate or nitrified or nitrify or		!
		nitrifies) SAME (oxidizing or oxidizes or	1	
i i	20070	oxidized or oxidating)	USPAT;	2002/10/23 14:2
-	38278	oxide with nitrogen	US-PGPUB	2002/10/25 14.2
_	239	(("oxide nitride" or "nitride oxide") SAME	USPAT;	2002/10/23 15:0
j	239	(nitridating or nitridation or nitriding	US-PGPUB	
		or nitrided or nitrification or nitricate	1	i .
į.		or nitridate or nitrified or nitrify or	I	
Į		nitrifies)) and (oxidizing or oxidizes or	1	1
l l		oxidized or oxidating)		
- 1	1		USPAT;	2002/10/23 15:0
			US-PGPUB	1

	22	2 ((("oxide nitride" or "nitride oxide")	USPAT;	2002/10/23 15:43
		SAME (nitridating or nitridation or	US-PGPUB	2002/10/23 13:43
		nitriding or nitrided or nitrification or	03-10100	
		nitricate or nitridate or nitrified or		
		nitrify or nitrifies)) and (oxidizing or		
		oxidizes or oxidized or oxidating)) not		
		((oxynitride or "oxy nitride" or SiON)		!
		SAME (nitridating or nitridation or		
		pitriding or mitridation or	!	
		nitriding or nitrided or nitrification or	1	1
		nitricate or nitridate or nitrified or	i	•
7		nitrify or nitrifies) SAME (oxidizing or		
1	0.7	oxidizes or oxidized or oxidating))		1
: -	21	0 (438/261).CCLS.	USPAT;	: 2002/10/23 15:40
			US-PGPUB	4
· -	2	8 '(((("oxide nitride" or "nitride oxide")	USPAT;	2002/10/23 15:44
		SAME (nitridating or nitridation or	US-PGPUB	1
		nitriding or nitrided or nitrification or	1	
1		nitricate or nitridate or nitrified or	İ	1
i i	!	nitrify or nitrifies)) and (oxidizing or		!
- 1		oxidizes or oxidized or oxidating)) not	1	1
1		((oxynitride or "oxy nitride" or SiON)	ļ.	
1	1	SAME (nitridating or nitridation or	i	
1	1	nitriding or nitrided or nitrification or	1	1
1	1	nitricate or nitridate or nitrified or	1	T
1	1	nitrify or nitrifies) SAME (oxidizing or	1	
,		oxidizes or oxidized or oxidating))) and		•
i	i i	(EPROM or "floating gate" or EEPROM)		i
1 -	1 12	(brkon of floating gate of EEPROM)	1	i .
	1 12	(oxide with nitrogen) and ("oxide nitride	USPAT;	2002/10/23 15:57
i	!	oxide" or ono or "oxide/nitride/oxide")	US-PGPUB	1
	ĺ	and (nitridation or nitridating or		
1		nitriding or nitrided or nitrification or	i .	1
1	1	nitricate or nitridate) and (((anneal or	1	1
		annealing) with (oxygen or "O.sub.2")) or	1	1
	!	(oxidizing or oxidation or oxidizes))	1	1
1 -	1 1	("5,296,411").PN.	USPAT;	2002/10/24 11:08
-	- 1		US-PGPUB	
-	1	("4567061" "4784975" "5296411"	USPAT	2002/10/24 11:16
1	1	"5306658" "5382550").PN.		2002/10/24 11:10 .
-	35	5296411.URPN.	USPAT	2002/10/24 11:20
-	18	5726087.URPN.	USPAT	2002/10/24 11:20
-	1 8	("4360900" "5060034" "5304829"	USPAT	2002/10/24 11:46
1		"5371028" "5536667" "5619051"	USPAI	2002/10/24 12:50
-	i	"5661056" "5888870").PN.		
l -	506	(interpoly or interpolysilicon or		
1		interlayer) with (ONO or "oxide nitride	USPAT;	2002/10/24 16:43 '
1	i	oxide")	US-PGPUB	
1 -	476			i .
1	4/6	((interpoly or interpolysilicon or	USPAT;	2002/10/24 16:15
1		interlayer) with (ONO or "oxide nitride	US-PGPUB	i
! _	4	oxide")) and (EPROM or "floating gate")		1
1 -	1 4	(((Interporty of Interportystricon or	USPAT;	2002/10/24 16:37
1	1	interlayer) with (ONO or "oxide nitride	US-PGPUB	
1		oxide")) and (EPROM or "floating gate"))		
	i	and ((oxide or dioxdie) with		1
		(dichlorosilane or "di chlorosilane" or		1
1	1	"dicholor silane" or DCS) with ("nitrous		
1		oxide" or "nitric oxide" or "N.sub.2 0" or		
!	1	"N.sub.20"))		
! -	5	("5208174" "5219774" "5619052"	USPAT	2002/10/24 16:27
1		"5677867" "5726087").PN.	OSFAI	2002/10/24 16:27
-	į n	(((interpoly or interpolysilicon or	HODAM.	2000 (20 (01 25
1	ı	interlayer) with (ONO or Touride	USPAT;	2002/10/24 16:38
1		interlayer) with (ONO or "oxide nitride	US-PGPUB	1
1	i	oxide")) and (EPROM or "floating gate"))		1
1	i	and ((oxide or dioxdie) with ("SiH.sub.2		
(i	C1.sub.2") with ("nitrous oxide" or	!	
1		"nitric oxide" or "N.sub.2 O" or	- 1	
		"N.sub.20"))		

	- 0	(((interpoly or interpolysilicon or interlayer) with (ONO or "oxide nitride oxide")) and (EPROM or "floating gate")) and ((oxide or dioxide) with ("SiH.sub.2 Cl.sub.2") with ("nitrous oxide" or "nitric oxide" or "sub.2 O or	USPAT; US-PGPUB	2002/10/24 16:39
÷-	14		USPAT;	2002/10/24 16:42
		interlayer) with (ONO or "oxide nitride oxide")) and (EPROM or "floating gate"))	US-PGPUB	
		and ((oxide or dioxide) Same ("SiH.sub.2 Cl.sub.2") same ("nitrous oxide" or "nitric oxide" or "N.sub.2 O" or "N.sub.20"))	i	
1-	10	("control gate" with doped with undoped) and (EPROM or "EEPROM")	USPAT; US-PGPUB	2002/10/24 18:01
-	29	(gate with doped with undoped) and (EPROM	USPAT;	2002/10/24 17:13
-		or "EEPROM") and (ONO or oxynitride) ((gate with doped with undoped) and (EPROM	US-PGPUB USPAT; US-PGPUB	2002/10/24 16:58
		or "EEPROM") and (ONO or oxynitride)) not (("control gate" with doped with undoped) and (EPROM or "EEPROM"))		
-	1	("5272099").PN.	USPAT; US-PGPUB	2002/10/24 17:09
-	11	("control gate" SAME (doped with undoped)) and (EPROM or EEPROM) and (ONO or oxynitride)	USPAT; US-PGPUB	2002/10/24 17:16
-	8	("control gate" SAME (doped with undoped)) and ("flash memory") and (ONO or oxynitride)	USPAT; US-PGPUB	2002/10/24 17:20
-	14	("control gate" SAME (doped with undoped)) and ("flash memory")	USPAT; US-PGPUB	2002/10/24 17:20
-	6		USPAT; US-PGPUB	2002/10/24 17:21
		(("control gate" SAME (doped with undoped)) and ("flash memory") and (ONO or 'oxynitride))		
-	37		USPAT; US-PGPUB	2002/10/24 17:43 .
-	10	("control gate" and (doped with undoped)) and 438/261.ccls.	USPAT; US-PGPUB	2002/10/24 17:47
-	64	("control gate" SAME (doped with undoped))	USPAT; US-PGPUB	2002/10/24 17:49
-	15	("control gate" with (doped with undoped))	USPAT; US-PGPUB	2002/10/24 18:08
-	49	(("control gate" SAME (doped with undoped))) not (("control gate" with (doped with undoped)))	USPAT; US-PGPUB	2002/10/24 17:49
-	2801	("control gate" with (polysilicon))	USPAT; US-PGPUB	2002/10/24 18:09
-	1352	(("control gate" with (polysilicon))) and eprom	USPAT; US-PGPUB	2002/10/24 18:09
-	86	(polysilicon with (doped) with (undoped)) and "control gate"	USPAT; US-PGPUB	2002/10/24 18:17
-	33	(polysilicon with (doped) with (undoped)) and EPROM	USPAT; US-PGPUB	2002/11/03 16:50
1-		(("in situ" or insitu or "in-situ") WITH (polysilicon or poly or silicon))	USPAT; US-PGPUB	2002/10/24 18:24
-	160	((("in situ" or insitu or "in-situ") WITH (polysilicon or poly or silicon))) SAME (doped with undoped)	USPAT; US-PGPUB	2002/10/24 18:25
-	13	(((("in situ" or insitu or "in-situ") WITH (polysilicon or poly or silicon)) SAME (doped with undoped)) and (eprom or eeprom)	USPAT; US-PGPUB	2002/10/24 18:43
1-	1	("6281078").PN.	USPAT; US-PGPUB	2002/10/24 18:46
-	627	(silane or "SiH.sub.4" or phosphene "PH.sub.3") same (polysilicon or silicon or poly) same undoped	USPAT; US-PGPUB	2002/10/24 18:47

- 254	((silane or "SiH.sub.4" or phosphene "PH.sub.3") same (polysilicon or silicon	USPAT; US-PGPUB	2002/10/24	18:47
- 55	or poly) same undoped) and memory (((silane or "SiH.sub.4" or phosphene			
50	"PH.sub.3") same (polysilicon or silicon	USPAT; US-PGPUB	2002/10/24	19:00
	or poly) same undoped) and memory) and (ono or "oxide nitride oxide")		İ	